**In the Claims**

1. (Currently amended) A hydrophobic Chemical mechanical planarization (HCMP) pad comprising:
an organic polymer; and
a metal agent, wherein the metal agent includes a metal B-diketonate.

2. (Currently amended) The HCMP pad of claim 1 wherein said organic polymer is one of ~~polyurethane~~, a polyurethane, or a polyether based material.

3. (Previously presented) The HCMP pad of claim 1 wherein said organic polymer is formed of a polyol and di-isocyanate.

4. (Currently amended) The HCMP pad of claim 1 wherein said organic polymer is reactive with one of a polyfunctional amine, a diamine, a triamine, a polyfunctional hydroxyl, and a ~~mixed~~ mixed functionality hydroxylamine.

5. (Previously presented) The HCMP pad of claim 1 further comprising a matrix material selected from a group consisting of a melamine, a polyester, a polysulfone, polyrinyl acetate, and a fluorinated hydrocarbon.

6. (Cancelled)

7. (Currently amended) The HCMP pad of claim ~~6~~ 1 wherein the metal B-diketonate includes one of cobalt, palladium, nickel, zinc, titanium, zirconium, hafnium, and copper.

8. (Currently amended) The HCMP pad of claim ~~6~~ 1 wherein the metal B-diketonate includes a side group selected from hydrogen, an aryl, a perfluoraryl, an alkyl, a perfluoroalkyl, and a t-butyl group.

9. (Currently amended) The HCMP pad of claim 1 for planarization of a semiconductor ~~wager~~ wafer, ~~the planarization of a semiconductor wafer~~, the planarization to isolate a metal feature in the semiconductor wafer.

10. (Previously presented) The HCMP pad of claim 9 wherein said metal agent includes a metal compatible with a metal of the metal feature.

11. (Previously presented) The HCMP pad of claim 9 to substantially retain a planarization characteristic during the planarization.

12. (Currently amended) The HCMP pad of claim 11 wherein the planarization characteristic is one of shearing, hardness, wearing, cross-linking, water uptake and electrical character.

13. (Previously presented) The HCMP pad of claim 9 to avoid substantial uptake of aqueous slurry during the planarization.

14. (Currently amended) A chemical mechanical planarization (CMP) material for forming a hydrophobic CMP (HCMP) pad consisting essentially of ~~and comprising~~:

a liquid urethane; and

a metal agent.

15. (Currently amended) The CMP material of claim 14 wherein the metal agent is metal agent is a B-diketonate ~~selected to effect cross-linking reactions during the forming~~.

16. (Currently amended) The CMP material of claim 14 wherein the metal agent is selected to increase thermal stability or effect cross-linking reaction during the forming.

17. (Currently amended) The CMP material of claim 14 wherein the ~~metal agent is a~~ B-diketonate has a side group selected from the group consisting of t-butyl and perfluoroalkyl ~~side group having one of t-butyl and perfluoroalkyl side groups~~.

18. (Withdrawn) A method comprising mixing an organic polymer and a metal agent to form a chemical mechanical planarization (CMP) material, wherein the metal agent is a B-diketonate.

19. (Withdrawn) The method of claim 18 further comprising:

adding a foaming agent and a curing agent to the CMP material;

reducing pressure around the CMP material; and

heating the CMP material.

20. (Withdrawn) The method of claim 19 further comprising sawing a hydrophobic CMP pad from a log formed of the CMP material.

21. (Withdrawn) A method comprising:

providing a hydrophobic chemical mechanical planarization (HCMP) pad according to claim 1; and

planarizing a semiconductor wafer with the HCMP pad.

22. (Withdrawn) The method of claim 21 wherein the planarizing further comprises:

delivering an aqueous slurry to a surface of the HCMP pad;

moving the HCMP pad in a first direction; and

moving the semiconductor wafer in a second direction different from the first direction.

23. (New) A method of forming a chemical mechanical planarization (CMP) material:
comprising: mixing components to form the CMP material wherein the CMP mixture consists essentially of an organic polymer and a metal agent.

24. (New) The method of claim 23 further comprising:

adding a foaming agent and a curing agent to the CMP material;

reducing pressure around the CMP material; and

heating the CMP material.

25. (New) The method of claim 24 further comprising sawing a hydrophobic CMP pad from a log formed of the CMP material.

26. (New) A method comprising:

providing a hydrophobic chemical mechanical planarization (HCMP) pad according to claim 14; and

planarizing a semiconductor wafer with the HCMP pad.

27. (NEW) The HCMP pad of claim 1 wherein said organic polymer is a urethane.